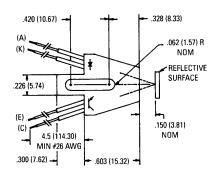
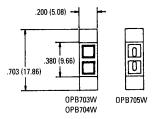


### **REFLECTIVE OBJECT SENSORS**

# OPB703W/OPB704W/OPB705W

## **PACKAGE DIMENSIONS**





FUNCTION WIRE COLOR

(C) COLLECTOR WHITE (E) EMITTER BLUE (K) CATHODE GREEN (A) ANODE ORANGE

#### NOTES

1. DIMENSIONS ARE IN INCHES (mm).

2. TOLERANCE IS ±.010 (.25)

OPB703W - IR TRANSPARENT DUST COVER OPB704W - IR TRANSPARENT DUST COVER OPB705W - OFFSET LENS

## **DESCRIPTION**

The OPB703W, OPB704W, and OPB705W consist of an infrared emitting diode and an NPN silicon phototransistor mounted side by side on a converging optical axis in a black plastic housing. The phototransistor responds to radiation from the emitting diode only when a reflective object passes within its field of view. The area of the optimum response approximates a circle .200" in diameter. Leads are 26 AWG, PVC insulation, 4.5" (114.3 mm) minimum length, stripped and tinned.

## **FEATURES**

- Phototransistor output.
- High Sensitivity.
- Low cost plastic housing.
- Pre wired with 4.5 inch, 26 gauge leads.
- OPB703W/OPB704W, dust cover; lens.
- OBP705W, offset lens.

ST4018



## **REFLECTIVE OBJECT SENSORS**

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C Unless	Otherwise Specified)
Storage Temperature	-40°C to + 85°C -40°C to + 85°C
Lead Temperature (Iron)	
INPUT DIODE Continuous Forward Current Reverse Voltage Power Dissipation	
OUTPUT TRANSISTOR Collector-Emitter Voltage Emitter-Collector Voltage Collector Current Power Dissipation	

PARAMETER	SYMBOL	MIN.	MAX.	UNITS	TEST CONDITIONS
INPUT DIODE					
Forward Voltage	$V_{\scriptscriptstyle F}$	_	1.70	٧	$I_F = 40 \text{ mA}$
Reverse Leakage Current	I <sub>R</sub>	_	100	μΑ	V <sub>R</sub> = 2.0 V
OUTPUT TRANSISTOR					
Emitter-Collector Breakdown	$BV_{eco}$	5	_	V	$I_E = 100 \ \mu A, Ee = 0$
Collector-Emitter Breakdown	BV <sub>c∈o</sub>	30	_	٧	$I_c = 100 \ \mu\text{A},  \text{Ee} = 0$
Collector-Emitter Leakage	I <sub>CEO</sub>	_	100	nA	V <sub>CE</sub> = 10.0 V, Ee = 0
COUPLED					
On-State Collector Current					
OPB703W	I <sub>C(ON)</sub>	200	_	μΑ	$I_F = 40 \text{ mA}, V_{CE} = 5 \text{ V}, D = .150''$
OPB704W	I <sub>C(ON)</sub>	200	_	μΑ	$I_F = 40 \text{ mA}, V_{CE} = 5 \text{ V}, D = .150''$
OPB705W	I <sub>C(ON)</sub>	100	_	μΑ	$I_F = 40 \text{ mA}, V_{CE} = 5 \text{ V}, D = .150''$
Crosstalk	I <sub>cx</sub>	_	20	μΑ	$I_{\rm F} = 40$ mA, $V_{\rm CE} = 5$ $V^{(7)}$

## NOTES

- 1. Derate power dissipation linearly 1.67 mW/°C above 25°C.
- 2. RMA flux is recommended.

- Methanol or Isopropyl alcohols are recommended as cleaning agents.
   Soldering iron tip ½6" (1.6 mm) from housing.
   D is the distance from the assembly face to the reflective surface.
   Measured using Eastman Kodak neutral test card with 90% diffused reflecting surface.
   Cross talk is the photocurrent measured with current to the input diode and no reflective surface.



## REFLECTIVE OBJECT SENSOR

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- A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.